GM	10	W
pp		

j

j=25 unless otherwise specified)

Symbol	Test Condition	Value		Unit
I_{GT}				
GT				
	$V_D=V_{DRM}$ =3.3kΩ	0.2V		
I	I .2 GT40 mA			
	Ope			
tonl	A=200mA 20mA			
toff	T j=25			
V	I =23A pp80	=2 .6V		
TO	Threshold voltage	=1 .77V		
R_D		=1 6Ω		
DRM	$V_D=V_{DRM}$ $V_R=V_{RM}$	T =25		
RRM T				

Symbol	Parameter	Value	Unit
R	junction to case (DC)	4.5	/W

Symbol	Parameter	Value (MAX)	Unit

FIG.1: Maximum power dissipation versus RMS on-state current

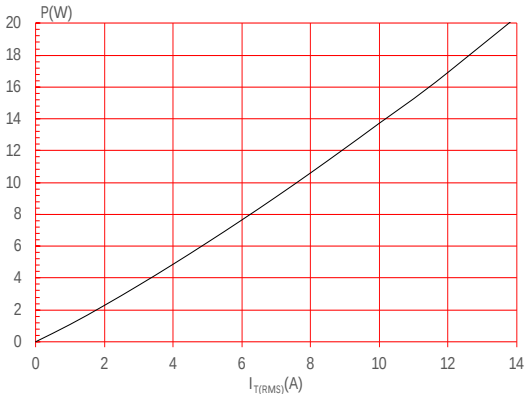


FIG.2: RMS on-state current versus case temperature

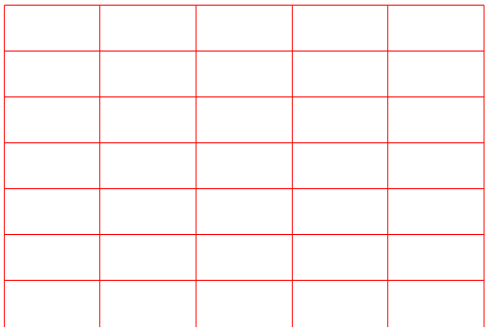


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

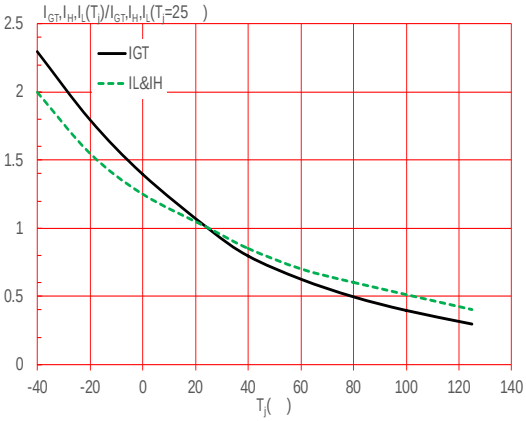
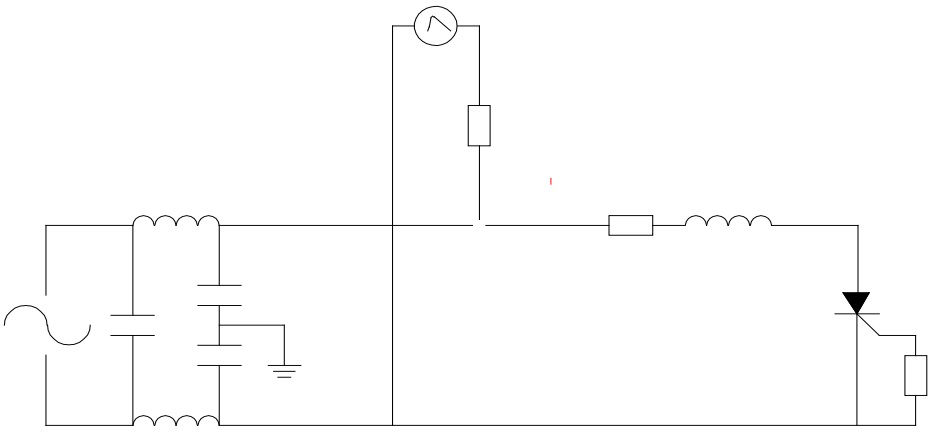


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.

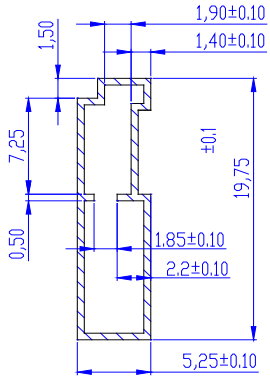


Order code	Voltage V_{DRM}/V_{RRM} (V)

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.15	0		0.006
B	0.66		0.86	0.026		0.034
C	0.40		0.60	0.016		0.024
D	5.90		6.30	0.232		0.248
E	6.40		6.80	0.252		0.268
G	4.47			0.053		0.6
G1	2.18		2.38	0.086		0.094
L						
L2				0.053		0.065

D




1,90±0.10
1,40±0.10
1,50
7,25
±0.1
19,75
0,50
1,85±0.10
2,2±0.10
5,25±0.10